

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A laser-markable structure for marking a semiconductor device comprising:
a marking tape comprising a material having a coefficient of thermal expansion substantially similar to the semiconductor device and antistatic properties; and
a multilayer adhesive used solely for laser marking a semiconductor device including:
a first outermost adhesive layer comprising a mixture of electromagnetic radiation-curable components ~~having properties of a first type, the electromagnetic radiation-curable components having properties of a first type comprising a first outermost adhesive layer providing a laser-markable surface that~~ upon exposure to an electromagnetic radiation source cure and bond ~~by curing and bonding~~ to at least a portion of a semiconductor device and form ~~forming~~ a mark on the semiconductor device by the electromagnetic radiation-curable components curing, bonding and remaining on the semiconductor device when a laser marks a semiconductor device; and
a second adhesive layer separate and distinct from the first outermost adhesive layer ~~having second properties different than the properties of the first type of the first outermost adhesive layer, the second adhesive layer~~ disposed between the tape and the first outermost adhesive layer, the second adhesive layer ~~having second properties comprising a second adhesive layer of~~ a mixture of electromagnetic radiation-curable components that upon exposing to radiation the second adhesive layer facilitate ~~facilitating~~ peeling of a flexible film material by a reduction in adhesiveness of the second adhesive layer with respect to the first outermost adhesive layer when the electromagnetic radiation from a laser strikes the second adhesive layer during laser marking a semiconductor device.
2. (Canceled)

3. (Previously Presented) The laser-markable structure of claim 1 , wherein at least a portion of the surface of a bare semiconductor device has grinding marks therein.

4. (Previously Presented) The laser-markable structure of claim 1 , wherein the first outermost adhesive layer comprises a permanently attached layer to at least a portion of the surface of the bare semiconductor device when the radiation-curable components are cured .

5. (Canceled)

6. (Previously Presented) The laser-markable structure of claim 4, wherein the first outermost adhesive layer includes a substantially homogenous surface disposed over at least a portion of the surface of the bare semiconductor die.

7. (Canceled)

8. (Previously Presented) The laser-markable structure of claim 1, wherein the tape comprises a flexible film material having translucent properties.

9. (Currently Amended) A tape for use in the laser marking of a semiconductor device comprising:

a marking tape having a coefficient of thermal expansion substantially similar to the semiconductor device; and

a multilayer adhesive used solely for laser marking a semiconductor device including:

a first outermost adhesive layer comprising a mixture of electromagnetic radiation-curable components having ~~properties of a first type comprising~~ a first outermost adhesive layer providing a mark on a laser-markable surface upon exposure thereof to electromagnetic radiation by curing and bonding to at least a portion of a semiconductor device by the electromagnetic radiation- curable

components curing, bonding, and remaining on the semiconductor device when a laser marks a semiconductor device; and

a second adhesive layer separate and distinct from the first outermost adhesive layer ~~having second properties different than properties of the first type of the first outermost adhesive layer~~, the second adhesive layer disposed between the flexible film material and the first outermost adhesive layer, the second adhesive layer ~~having second properties comprising a second adhesive layer of a mixture of electromagnetic radiation-curable components~~ that upon exposing to radiation the second adhesive layer ~~facilitate~~ facilitating peeling of a flexible film material by a reduction in adhesiveness of the second adhesive layer when laser marking a semiconductor device.

10. (Canceled)

11. (Previously Presented) The tape of claim 9, wherein the portion of the surface of the semiconductor device has grinding marks therein.

12. (Previously Presented) The tape of claim 9, wherein the first outermost adhesive layer is permanently attached to at least a portion of the surface of the bare semiconductor die when the radiation-curable components are in a cured state.

13. (Canceled)

14. (Previously Presented) The tape of claim 12, wherein the first outermost adhesive layer comprises a substantially homogenous surface disposed over at least a portion of the surface of the bare semiconductor die suitable for providing a mark by laser marking.

15 (Canceled)

16. (Previously Presented) The tape of claim 9, wherein the flexible film material comprises a flexible film material having translucent properties.

17. (Currently Amended) A tape for use in the marking of a semiconductor device comprising:

a marking tape having a material having a coefficient of thermal expansion substantially similar to the semiconductor device and antistatic properties; and

at least two layers of adhesive used solely for laser marking a semiconductor device including:

a first outermost adhesive layer comprising a mixture of electromagnetic

~~radiation-curable components having properties of a first type comprising a first~~

~~outermost adhesive layer~~ providing a mark on a surface upon exposure thereof to

electromagnetic radiation by curing and bonding to at least a portion of a

semiconductor device, the radiation-curable components forming the mark by

curing and bonding to a surface of the semiconductor device when a laser marks a

semiconductor device; and

a second adhesive layer separate and distinct from the first outermost adhesive layer

~~having second properties different than the properties of the first type of the first~~

~~outermost adhesive layer~~, the second adhesive layer disposed between the film

material and the first outermost adhesive layer, the second adhesive layer having

second properties comprising a ~~second adhesive layer~~ of a mixture of

electromagnetic radiation-curable components that upon exposing to radiation the

second adhesive layer solely facilitate ~~facilitating~~ peeling of a flexible film

material by a reduction in adhesiveness of the second adhesive layer when laser

marking a semiconductor device by the electromagnetic radiation from the laser

striking the second adhesive layer.

18. (Canceled)

19. (Previously Presented) The tape of claim 17, wherein the portion of the surface of the semiconductor device has grinding marks therein.

20. (Previously Presented) The tape of claim 17, wherein the first outermost adhesive layer is permanently attached to at least a portion of the surface of the bare semiconductor die when the radiation-curable components are in a cured state.

21. (Canceled)

22. (Previously Presented) The tape of claim 20, wherein the electromagnetic radiation-curable components form a substantially homogenous surface upon exposure to an electromagnetic radiation source, the substantially homogenous surface being disposed over the at least the portion of the surface of a bare semiconductor die, the substantially homogenous surface being suitable for laser marking for forming a mark on the surface of the bare semiconductor die.

23. (Canceled)

24. (Previously Presented) The tape of claim 17, wherein the film material comprises a film material having translucent properties.